



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
60V	5.0Ω @ $V_{GS} = 10V$	320mA
000	7.5Ω @ V _{GS} = 5V	260mA

Description and Applications

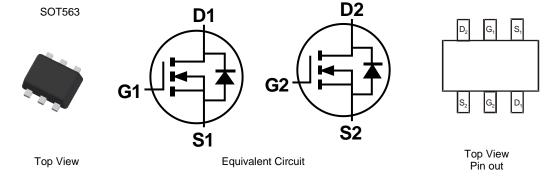
This MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Features and Benefits

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (Approximate)



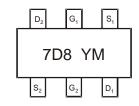
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN67D8LV-7	SOT563	3000/Tape & Reel
DMN67D8LV-13	SOT563	10000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



7D8 = Product Type Marking Code YM = Date Code Marking Y = Year ex: B = 2014 M = Month ex: 9 = September

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	В	С	D	Е	F	G	Н	ı	J	K	L	М

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V_{DSS}	60	V	
Gate-Source Voltage		V_{GSS}	±20	V	
Continuous Drain Current (Note 6) V _{GS} = 10V	I _D	320 260	mA		
Maximum Continuous Body Diode Forward Curren	t (Note 6)	I _S	0.5	Α	
Pulsed Drain Current (10µs pulse, duty cycle = 1%) (Note 6)		I _{DM}	0.8	А

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

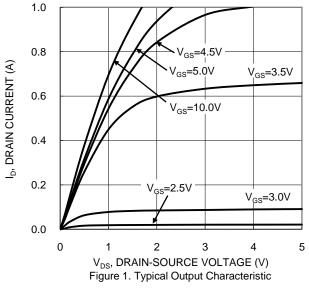
Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		P_{D}	520	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	242	°C/W
Total Power Dissipation (Note 6)		P _D	800	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	159	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

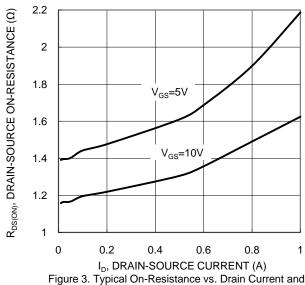
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

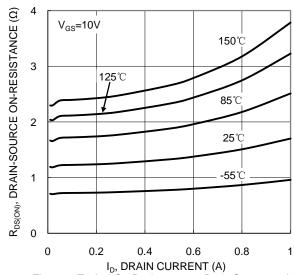
Chamastanistis	Complete	Min	T	Mari	11	Took Condition
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						1
Drain-Source Breakdown Voltage	BV _{DSS}	60			V	$V_{GS} = 0V$, $I_D = 10\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1.0	μΑ	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	Igss		_	±10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1.0		2.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance			3.2	7.5	Ω	$V_{GS} = 5.0V, I_D = 0.05A$
Static Dialii-Source Off-Resistance	R _{DS(ON)}	_	1.5	5.0	52	$V_{GS} = 10V, I_D = 0.5A$
Forward Transconductance	g FS	80			mS	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage	V_{SD}		0.78	1.5	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	_	22	_	pF	V 05V V 0V
Output Capacitance	Coss		4.1	1	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}		2.5		pF	1 = 1.0IVII IZ
Gate Resistance	R_{g}		120		Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge (V _{GS} = 4.5V)	Q_g	_	361	_		
Total Gate Charge (V _{GS} = 10V)	Q_g	_	821	_	рС	$V_{DS} = 10V, I_{D} = 250mA$
Gate-Source Charge	Q_{gs}	_	162	_	pc	VDS = 10V, ID = 230IIIA
Gate-Drain Charge	Q_gd	_	116	_		
Turn-On Delay Time	t _{D(ON)}	_	2.8	_		V 20V I 0.24
Turn-On Rise Time	t _R	_	3.0	_	ns	$V_{DD} = 30V, I_D = 0.2A,$ $R_L = 150\Omega, V_{GEN} = 10V, R_{GEN} =$
Turn-Off Delay Time	t _{D(OFF)}	_	7.6	_	115	$R_L = 150\Omega$, $V_{GEN} = 10V$, $R_{GEN} = 125\Omega$
Turn-Off Fall Time	t _F	_	5.6	_		2032

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.



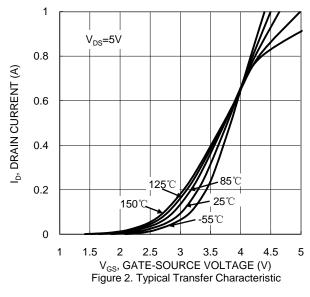


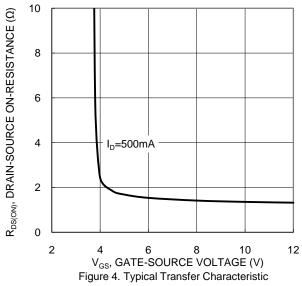




Gate Voltage

Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature





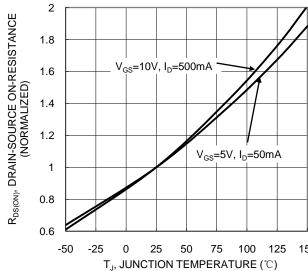


Figure 6. On-Resistance Variation with Junction Temperature



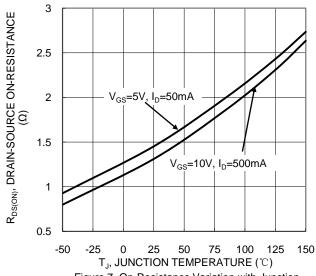
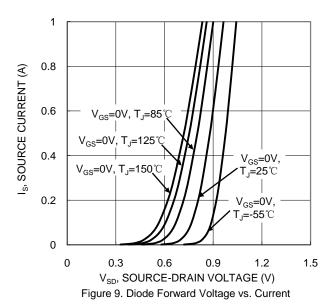
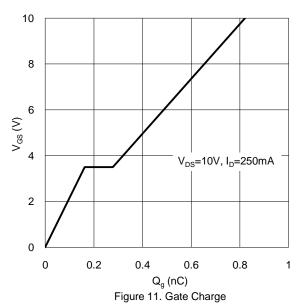


Figure 7. On-Resistance Variation with Junction Temperature





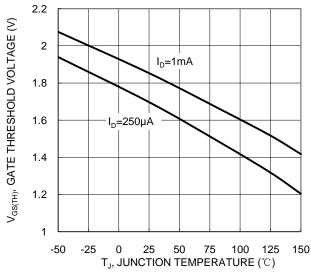
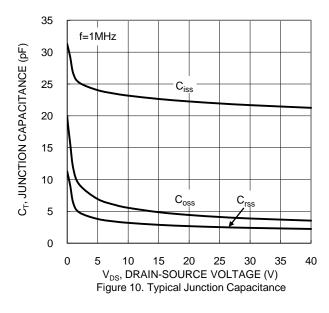
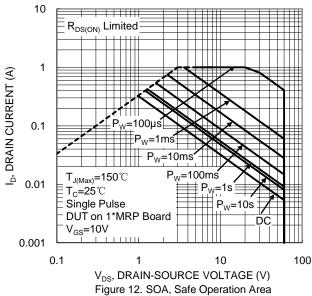


Figure 8. Gate Threshold Variation vs. Junction Temperature







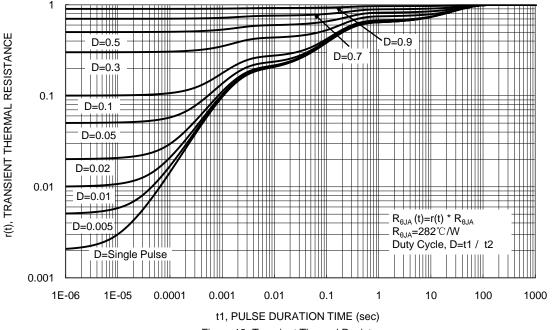
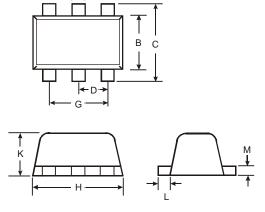


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

SOT563



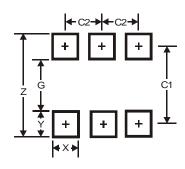
	SOT563								
Dim	Min	Max	Тур						
Α	0.15	0.30	0.20						
В	1.10	1.25	1.20						
С	1.55	1.70	1.60						
D	-	-	0.50						
G	0.90	1.10	1.00						
Н	1.50	1.70	1.60						
K	0.55	0.60	0.60						
L	0.10	0.30	0.20						
М	0.10	0.18	0.11						
All	Dimens	sions in	mm						



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

SOT563



Dimensions	Value (in mm)
Z	2.2
G	1.2
Х	0.375
Υ	0.5
C1	1.7
C2	0.5

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